



STPS130A/U

SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	1 A
V_{RRM}	30 V
$V_F (max)$	0.46 V

FEATURES AND BENEFITS

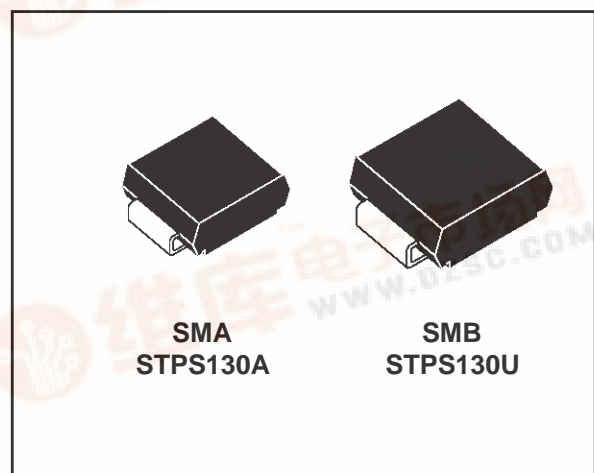
- LOW DROP FORWARD VOLTAGE FOR LESS POWER DISSIPATION AND LOW LEAKAGE
- OPTIMIZED CONDUCTION / REVERSE LOSSES TRADE-OFF ALLOWING THE HIGHEST EFFICIENCY IN APPLICATION
- SURFACE MOUNT MINIATURE PACKAGE

DESCRIPTION

Single Schottky rectifier suited to Switched Mode Power Supplies and high frequency DC/DC converters.

Packaged in SMA or SMB(*), this device is especially intended for use in parallel with MOSFETs in synchronous rectification and low voltage secondary rectification.

(*) in accordance with DO214AA and DO214AC JEDEC



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	30	V
$I_{F(RMS)}$	RMS forward current	7	A
$I_{F(AV)}$	Average forward current	$T_L = 135^\circ C$ $\delta = 0.5$	1 A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	45 A
I_{RRM}	Repetitive peak reverse current	$t_p = 2 \mu s$ $F = 1 \text{ kHz}$	1 A
I_{RSM}	Non repetitive peak reverse current	$t_p = 100 \mu s$ square	1 A
T_{stg}	Storage temperature range	- 65 to + 150	$^\circ C$
T_j	Maximum junction temperature	150	
dV/dt	Critical rate of rise of reverse voltage	10000	V/ μs

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THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R _{th(j-l)}	Junction to lead	SMA	30	°C/W
		SMB	25	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Tests Conditions	Tests Conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	T _j = 25°C	V _R = 30V			10	μA
		T _j = 125°C			1.5	10	mA
V _F **	Forward voltage drop	T _j = 25°C	I _F = 1 A			0.55	V
		T _j = 125°C	I _F = 1 A		0.37	0.46	
		T _j = 25°C	I _F = 2 A			0.63	
		T _j = 125°C	I _F = 2 A		0.45	0.55	

Pulse test : * tp = 380 μs, δ < 2%

** tp = 5ms, δ < 2%

To evaluate the maximum conduction losses use the following equation :

$$P = 0.37 \times I_{F(AV)} + 0.090 \times I_{F(RMS)}^2$$

Fig. 1: Average forward power dissipation versus average forward current.

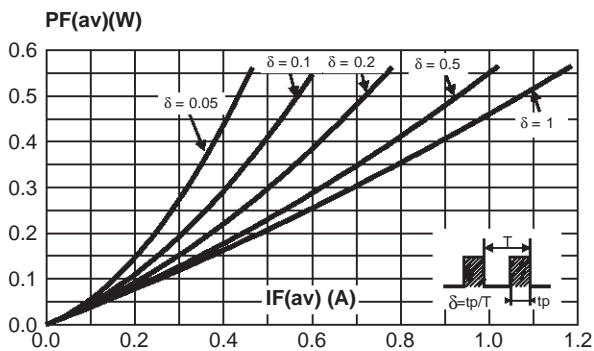


Fig. 2: Average forward current versus ambient temperature (δ=0.5).

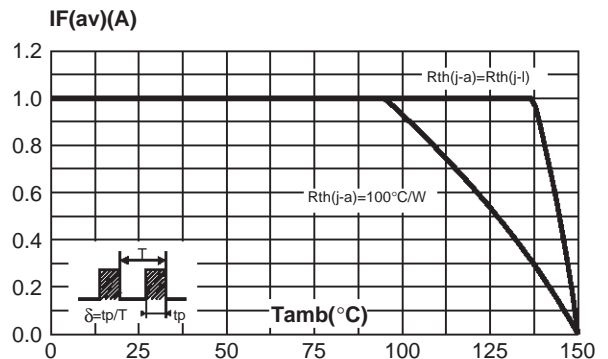


Fig. 3-1: Non repetitive surge peak forward current versus overload duration (maximum values) (SMB).

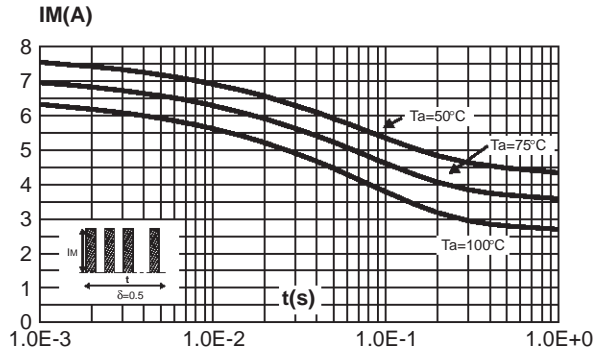


Fig. 3-2: Non repetitive surge peak forward current versus overload duration (maximum values) (SMA).

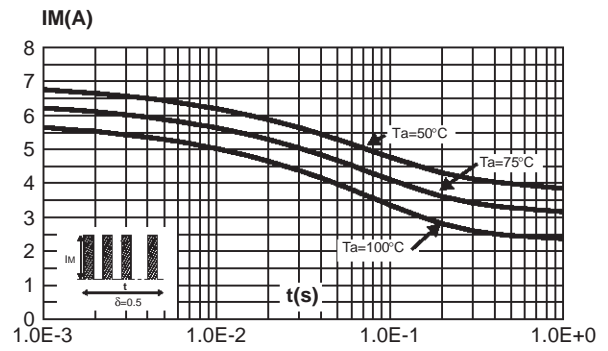


Fig. 4-1: Relative variation of thermal impedance junction to ambient versus pulse duration (epoxy printed circuit board, S(Cu)=35mm, recommended pad layout). (SMB)

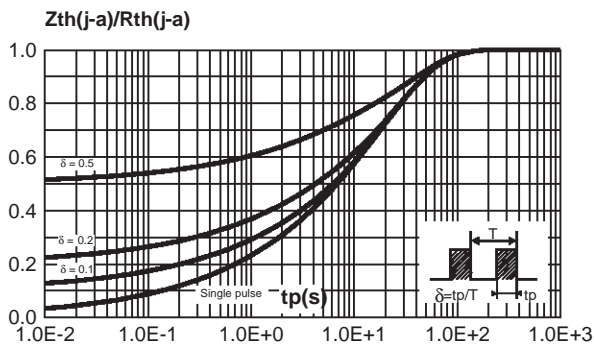


Fig. 4-2: Relative variation of thermal impedance junction to ambient versus pulse duration (epoxy printed circuit board, S(Cu)=35mm, recommended pad layout). (SMA)

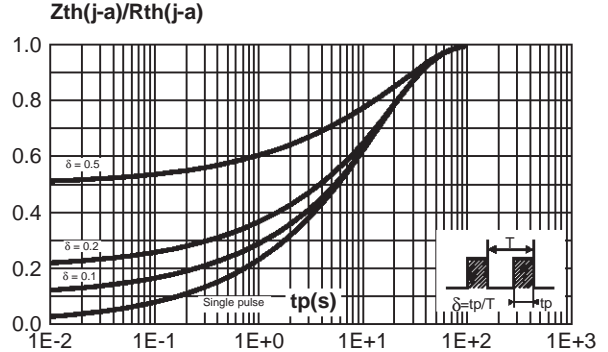


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values).

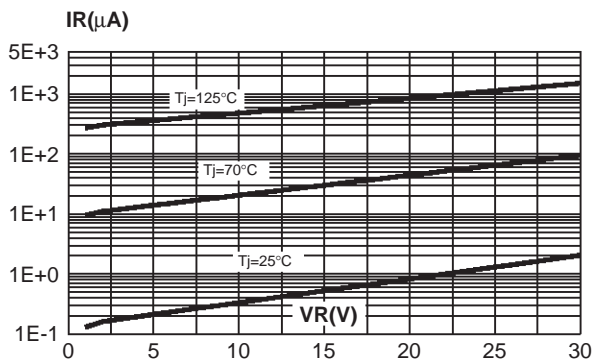
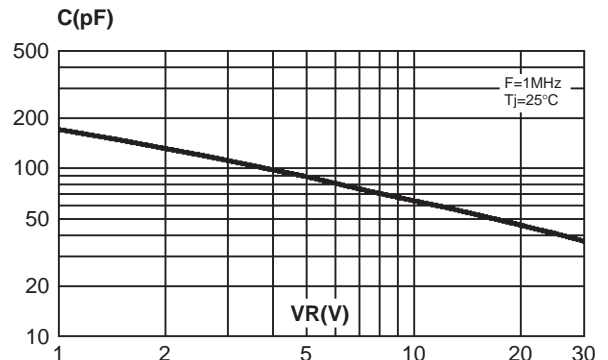


Fig. 6: Junction capacitance versus reverse voltage applied (typical values).



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Fig. 7: Forward voltage drop versus forward current (maximum values).

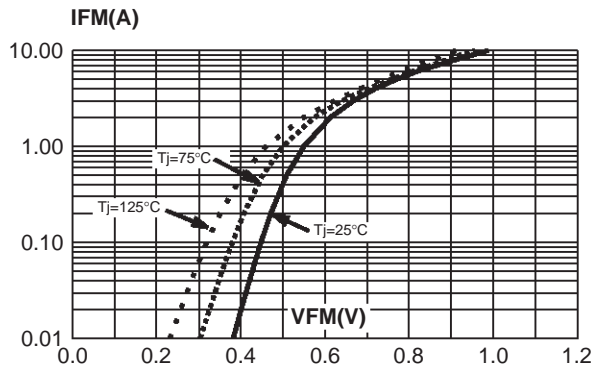


Fig. 8-1: Thermal resistance junction to ambient versus copper surface under each lead (Epoxy printed circuit board, copper thickness: 35µm).(SMB)

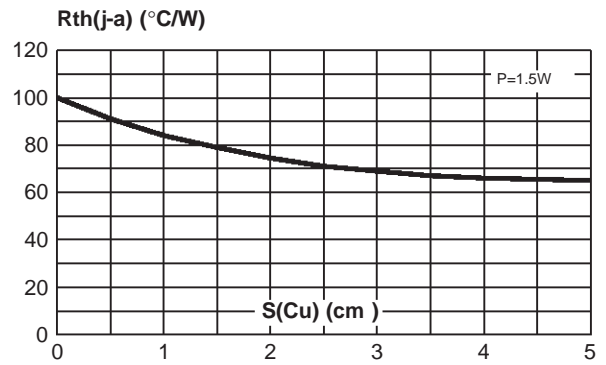
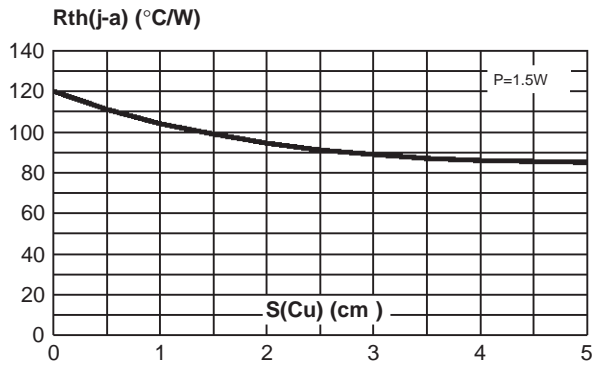
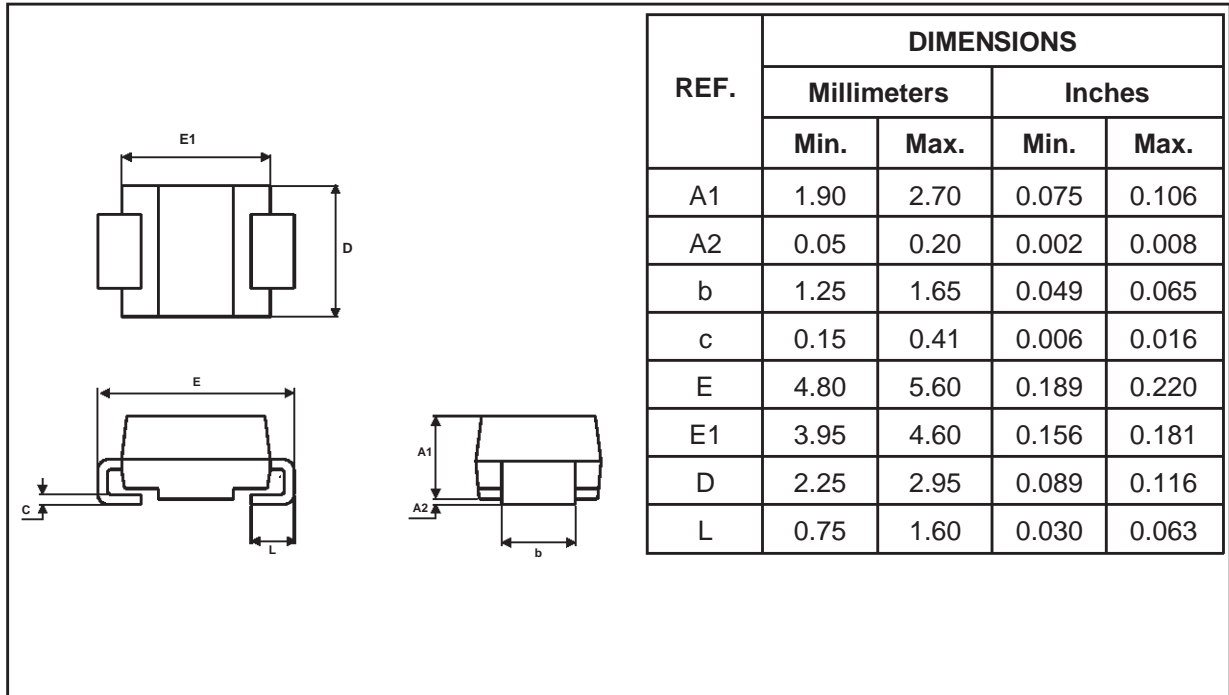


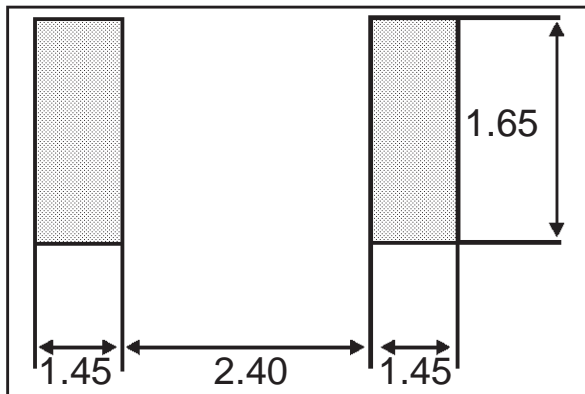
Fig. 8-2: Thermal resistance junction to ambient versus copper surface under each lead (Epoxy printed circuit board, copper thickness: 35µm).(SMA)



PACKAGE MECHANICAL DATA
SMA



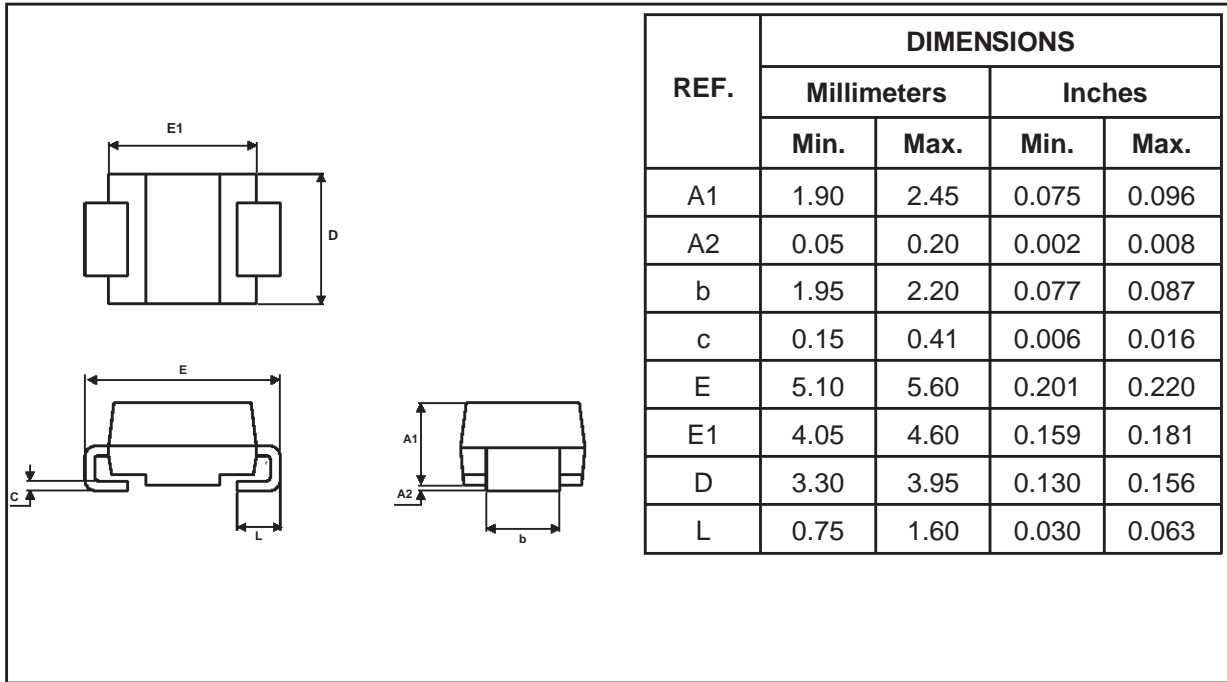
FOOT PRINT (in millimeters)



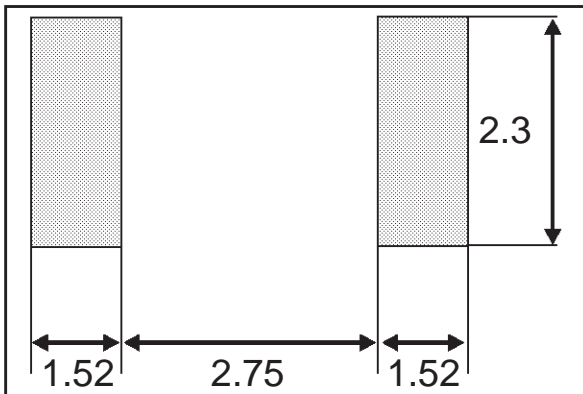
- **Marking:** S130
- Cathode band indicates cathode

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PACKAGE MECHANICAL DATA SMB



FOOT PRINT (in millimeters)



- **Marking:** G12
- Cathode band indicates cathode

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